Damir Borovac

List of Publications by Year
in descending order

22 papers	142 citations	1306789 7 h-index	1199166 12 g-index
22 all docs	22 docs citations	22 times ranked	112 citing authors

#	Article	IF	Citations
1	Dilute-As InGaNAs/GaN Quantum Wells for High-Efficiency Red Emitters. IEEE Journal of Quantum Electronics, 2022, 58, 1-6.	1.0	1
2	Prospects for hole doping in dilute-anion III-nitrides. Applied Physics Letters, 2021, 118, .	1.5	1
3	Thermal oxidation rates and resulting optical constants of Al0.83In0.17N films grown on GaN. Journal of Applied Physics, 2021, 129, .	1.1	6
4	Recombination Rates of In_xGa_{1â^'x}N/Al_yGa_{1â^'y}N/GaN Multiple Quantum Wells Emitting From 640 to 565 nm. IEEE Journal of Quantum Electronics, 2021, 57, 1-7.	1.0	2
5	Gain Properties of Dilute-As InGaNAs Quantum Wells for Red-Emitting Lasers. , 2021, , .		0
6	On the thermal stability of nearly lattice-matched AlInN films grown on GaN via MOVPE. Journal of Crystal Growth, 2020, 533, 125469.	0.7	11
7	Low background doping in AlInN grown on GaN via metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2020, 548, 125847.	0.7	7
8	Electronic properties of dilute-As InGaNAs alloys: A first-principles study. Journal of Applied Physics, 2020, 127, .	1.1	2
9	Controlled growth of InGaN quantum dots on photoelectrochemically etched InGaN quantum dot templates. Journal of Crystal Growth, 2020, 540, 125652.	0.7	3
10	AlInN/GaN diodes for power electronic devices. Applied Physics Express, 2020, 13, 091006.	1.1	6
11	Thermal Oxidation of AlInN for III-Nitride Electronic and Optoelectronic Devices. ACS Applied Electronic Materials, 2019, 1, 1367-1371.	2.0	12
12	Band Anti-Crossing Model in Dilute-As GaNAs Alloys. Scientific Reports, 2019, 9, 5128.	1.6	9
13	Investigation of Band Anticrossing Parameters for Dilute-Anion III-Nitride Alloys. , 2019, , .		0
14	Recombination rates in green-yellow InGaN-based multiple quantum wells with AlGaN interlayers. Journal of Applied Physics, 2019, 126, .	1.1	12
15	First-Principle Study of the Optical Properties of Dilute-P GaN1â^'xPx Alloys. Scientific Reports, 2018, 8, 6025.	1.6	6
16	Experimental Studies of Delta-InN Incorporation in InGaN Quantum Well for Long Wavelength Emission. , 2018, , .		1
17	First-principle electronic properties of dilute-P AlNP deep ultraviolet semiconductor. AIP Advances, 2018, 8, .	0.6	4
18	Investigations of the Optical Properties of GaNAs Alloys by First-Principle. Scientific Reports, 2017, 7, 17285.	1.6	7

#	Article	IF	Citations
19	InGaN/Dilute-As GaNAs Interface Quantum Well for Red Emitters. Scientific Reports, 2016, 6, 19271.	1.6	29
20	Dilute-As AlNAs Alloy for Deep-Ultraviolet Emitter. Scientific Reports, 2016, 6, 22215.	1.6	8
21	First-Principle Electronic Properties of Dilute-P GaN1â^'xPx Alloy for Visible Light Emitters. Scientific Reports, 2016, 6, 24412.	1.6	15
22	Dilute-anion III-nitride: A potential visible light emitter. , 2016, , .		0